

Application No. 10/700,429
Reply to Office Action of July 11, 2005
Amendment dated January 11, 2006

Amendments to the Specification

insert yk 1/21/2010

Please ~~replace the paragraph that was inserted~~
before the first line of the specification with the following ~~amended version of that paragraph~~ ^{yn}:

This application is a continuation of copending,
commonly assigned United States Patent Application
No. 09/775,597, filed February 5, 2001, now U.S. Patent
No. 6,682,981, which is a continuation of United States
Patent Application No. 09/027,959, filed February 23, 1998,
now abandoned, which is a division of United States Patent
Application No. 08/850,749, filed May 2, 1997, now U.S.
Patent No. 5,985,693, which is a continuation of United
States Patent Application No. 08/315,905, filed September 30,
1994, now U.S. Patent No. 5,869,354, which is a division of
United States Patent Application No. 07/865,412, filed April
8, 1992, now U.S. Patent No. 5,354,695, all of which are
incorporated by reference herein in their entireties.

Please replace the paragraph at page 24,
lines 10-34 with the following amended version of that
paragraph:

The Air Tunnel structure in one embodiment is
fabricated with CVD processing techniques; alternatively, ECR
(Electron-Cyclotron-Resonance) plasma CVD processing may soon
provide an alternative deposition method. The gaseous
dielectric separation of a conductor or a semiconductor
device is accomplished by forming a sacrificial CVD film of
a-Si, polysilicon or alternate material (typically dielectric
material) that can be deposited by CVD means and selectively
etched versus the other MDI circuit membrane material layers.